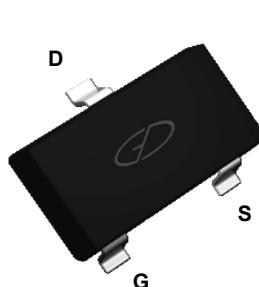
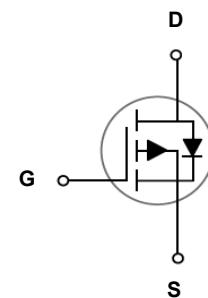


Main Product Characteristics

BV _{DSS}	-60V
R _{DS(ON)}	95mΩ
I _D	-3A



SOT-23



Schematic Diagram

Features and Benefits

- Advanced MOSFET process technology
- Ideal for high efficiency switched mode power supplies
- Low on-resistance with low gate charge
- Fast switching and reverse body recovery



Description

The GSFC0603 utilizes the latest techniques to achieve high cell density and low on-resistance. These features make this device extremely efficient and reliable for use in high efficiency switch mode power supply and a wide variety of other applications.

Absolute Maximum Ratings ($T_C=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Max.	Unit
Drain-Source Voltage	V _{DS}	-60	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous ($T_A=25^\circ\text{C}$)	I _D	-3	A
Drain Current-Continuous ($T_A=70^\circ\text{C}$)		-2.4	
Drain Current-Pulsed ¹	I _{DM}	-12	A
Single Pulse Avalanche Energy ²	E _{AS}	25	mJ
Single Pulse Avalanche Current ²	I _{AS}	-18	A
Power Dissipation ($T_A=25^\circ\text{C}$)	P _D	1.56	W
Power Dissipation-Derate above 25°C		0.0125	W/°C
Thermal Resistance, Junction-to-Ambient	R _{θJA}	80	°C/W
Operating Junction Temperature Range	T _J	-55 To +150	°C
Storage Temperature Range	T _{STG}	-55 To +150	°C

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
On/Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=-250\mu\text{A}$	-60	-	-	V
Drain-Source Leakage Current	$I_{\text{DS}(\text{S})}$	$V_{\text{DS}}=-60\text{V}, V_{\text{GS}}=0\text{V}, T_J=25^\circ\text{C}$	-	-	-1	μA
		$V_{\text{DS}}=-48\text{V}, V_{\text{GS}}=0\text{V}, T_J=125^\circ\text{C}$	-	-	-10	μA
Gate-Source Leakage Current	I_{GSS}	$V_{\text{GS}}=\pm20\text{V}, V_{\text{DS}}=0\text{V}$	-	-	±100	nA
Static Drain-Source On-Resistance	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}}=-10\text{V}, I_{\text{D}}=-2\text{A}$	-	79	95	$\text{m}\Omega$
		$V_{\text{GS}}=-4.5\text{V}, I_{\text{D}}=-1\text{A}$	-	99	129	
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{GS}}=V_{\text{DS}}, I_{\text{D}}=-250\mu\text{A}$	-1.2	-1.6	-2.5	V
Forward Transconductance	g_{fs}	$V_{\text{DS}}=-10\text{V}, I_{\text{D}}=-1\text{A}$	-	3	-	S
Dynamic and Switching Characteristics						
Total Gate Charge ^{3,4}	Q_g	$V_{\text{DS}}=-30\text{V}, I_{\text{D}}=-1\text{A}$ $V_{\text{GS}}=-10\text{V}$	-	10	15	nC
Gate-Source Charge ^{3,4}	Q_{gs}		-	1.6	2.4	
Gate-Drain Charge ^{3,4}	Q_{gd}		-	3	4.5	
Turn-On Delay Time ^{3,4}	$t_{\text{d}(\text{on})}$	$V_{\text{DD}}=-30\text{V}, R_{\text{G}}=6\Omega$ $V_{\text{GS}}=-10\text{V}, I_{\text{D}}=-1\text{A}$	-	8	12	nS
Rise Time ^{3,4}	t_r		-	15.4	23	
Turn-Off Delay Time ^{3,4}	$t_{\text{d}(\text{off})}$		-	42.8	64	
Fall Time ^{3,4}	t_f		-	8.4	13	
Input Capacitance	C_{iss}	$V_{\text{DS}}=-30\text{V}, V_{\text{GS}}=0\text{V}, F=1\text{MHz}$	-	785	1178	pF
Output Capacitance	C_{oss}		-	175	263	
Reverse Transfer Capacitance	C_{rss}		-	112	168	
Drain-Source Diode Characteristics and Maximum Ratings						
Continuous Source Current	I_s	$V_G=V_D=0\text{V},$ Force Current	-	-	-3	A
Pulsed Source Current	I_{SM}		-	-	-6	A
Diode Forward Voltage	V_{SD}	$V_{\text{GS}}=0\text{V}, I_{\text{S}}=-1\text{A}, T_J=25^\circ\text{C}$	-	-	-1	V

Note:

1. Repetitive rating: Pulsed width limited by maximum junction temperature.
2. $V_{\text{DD}}=-25\text{V}, V_{\text{GS}}=-10\text{V}, L=0.1\text{mH}, I_{\text{AS}}=-18\text{A}, R_{\text{G}}=25\Omega$, starting $T_J=25^\circ\text{C}$.
3. Pulse test: pulse width $\leq 300\text{us}$, duty cycle $\leq 2\%$.
4. Essentially independent of operating temperature.

Typical Electrical and Thermal Characteristic Curves

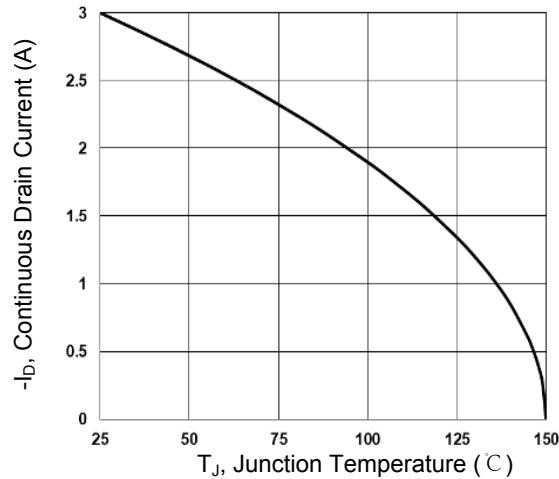


Figure 1. Continuous Drain Current vs. T_J

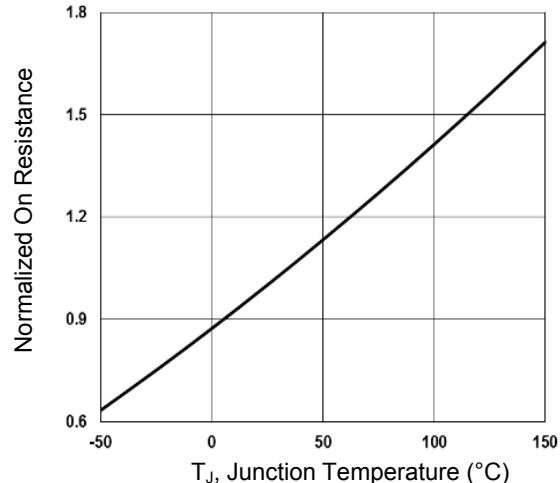


Figure 2. Normalized R_{DS(on)} vs. T_J

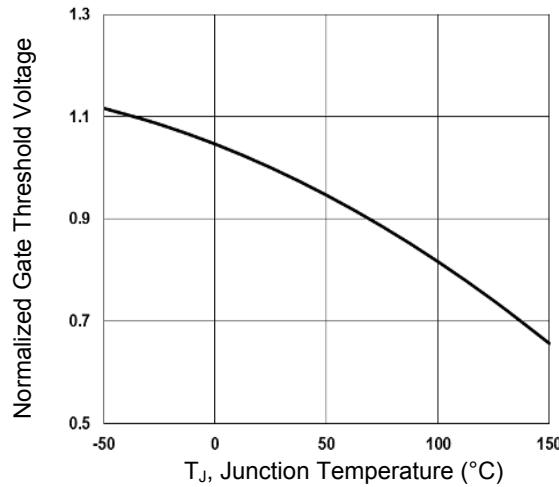


Figure 3. Normalized V_{th} vs. T_J

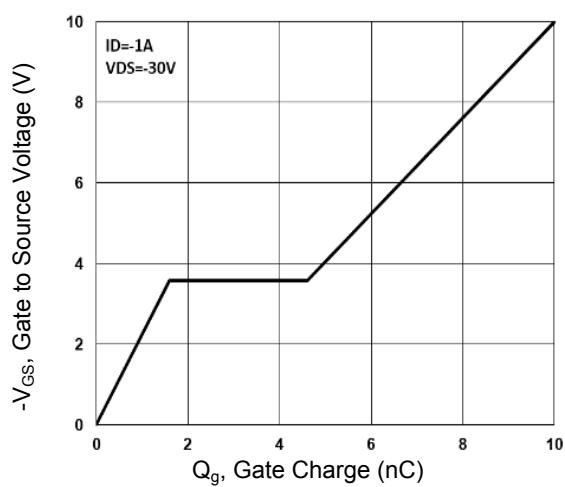


Figure 4. Gate Charge Waveform

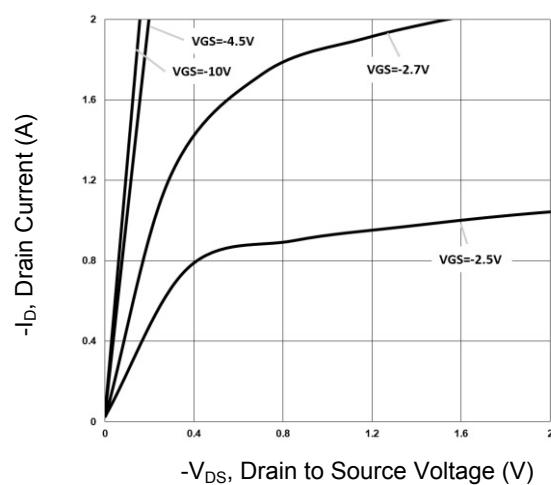


Figure 5. Typical Output Characteristics

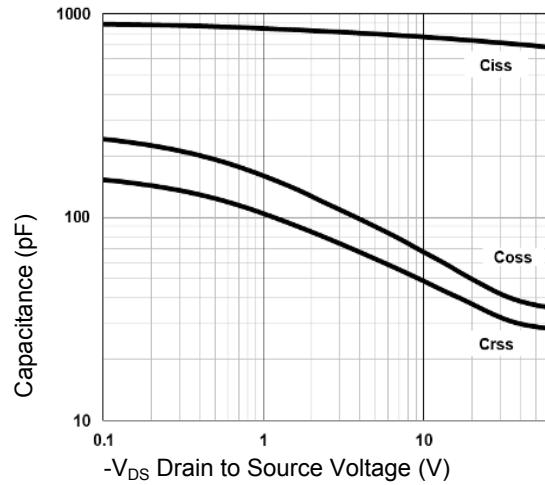


Figure 6. Capacitance Characteristics

Typical Electrical and Thermal Characteristic Curves

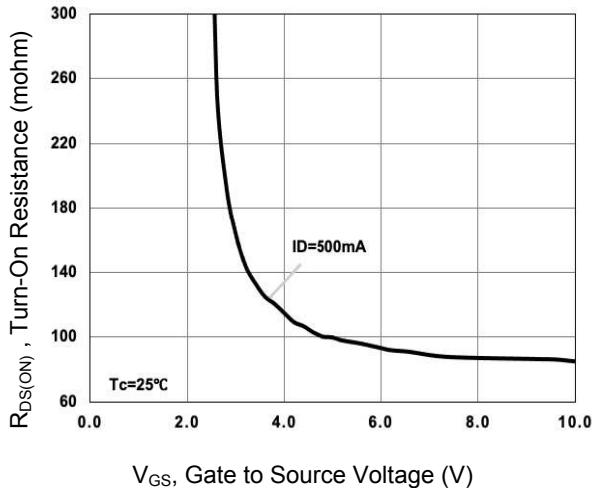


Figure 7. Turn-On Resistance vs. V_{GS}

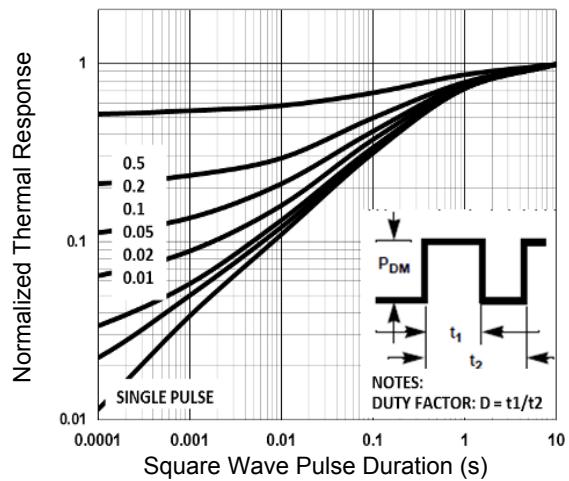


Figure 8. Normalized Transient Impedance

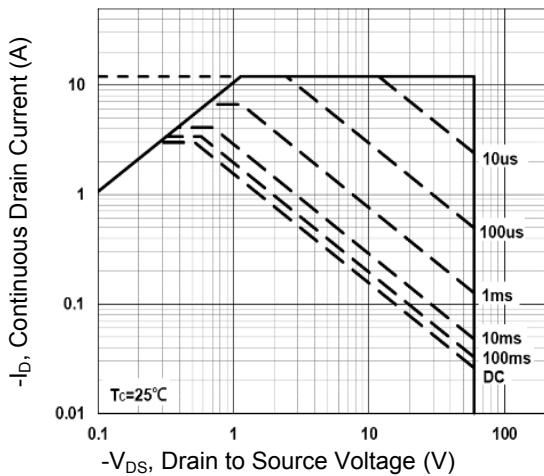


Figure 9. Maximum Safe Operation Area

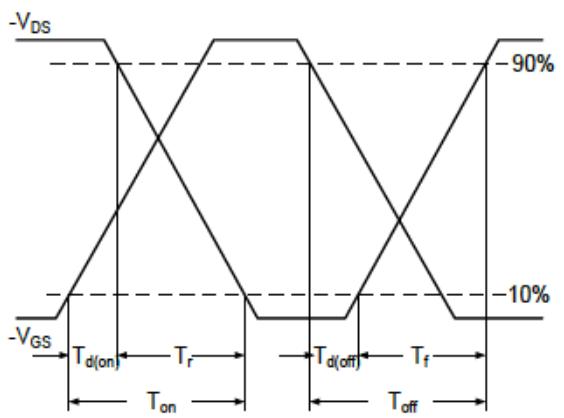


Figure 10. Switching Time Waveform

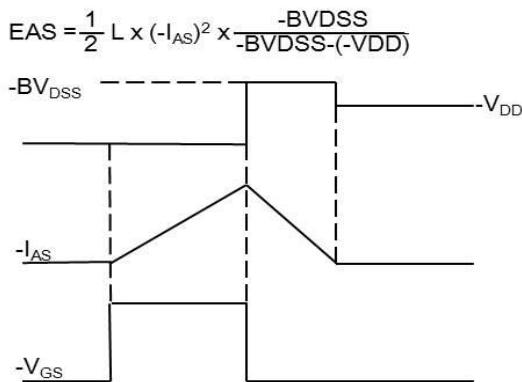
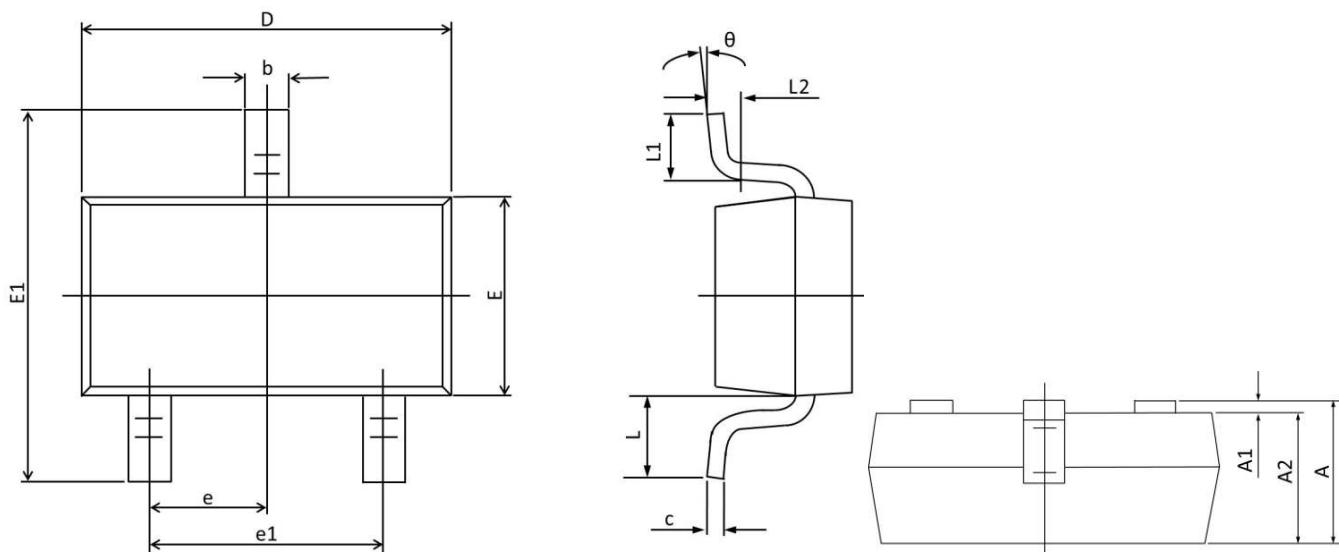


Figure 11. EAS Waveform

Package Outline Dimensions (SOT-23)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.450	0.041	0.057
A1	-	0.150	-	0.006
A2	0.900	1.300	0.035	0.051
b	0.300	0.490	0.012	0.019
c	0.100	0.200	0.004	0.008
D	2.820	3.050	0.111	0.120
E	1.500	1.750	0.059	0.069
E1	2.600	3.000	0.102	0.118
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.700 REF.		0.028 REF.	
L1	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

Order Information

MPN	Package	Marking	Quantity	HSF Status
GSFC0603	SOT-23	6	3000pcs / Reel	RoHS compliant